
ERRATA

STOICHIOMETRIC AND STRUCTURAL ORIGIN OF ELECTRONIC STATES AT THE Pd₂Si-Si INTERFACE. P. S. Ho, P. E. Schmid, and H. Föll [Phys. Rev. Lett. 46, 782 (1981)].

On page 784, seven lines from the bottom of the first column, "interfacial silicide layer" should read "interfacial silicide layer (about 2-3 monolayers)."

LOW-ANGULAR-MOMENTUM CUTOFF IN STATISTICAL HEAVY-ION PROCESSES. A. Szanto de Toledo and Mahir S. Hussein [Phys. Rev. Lett. 46, 985 (1981)].

On page 985, line 16 of the left-hand column, the relation $\frac{1}{2}m(V_F + V_{rel})^2 \geq B$ should read $\frac{1}{2}m(V_F + V_{rel})^2 \geq B + \frac{1}{2}mV_F^2$.

On page 988, Ref. 12, the cross-section formula given in the footnote should read

$$\frac{d\sigma}{d\Omega} \propto \frac{1}{\sin\theta} \left\{ 1 + \frac{1}{2} \left[\sin(2L_0\theta) \frac{2\pi(\Delta L/2.9)\theta}{\sinh[2\pi(\Delta L/2.9)\theta]} - \{\sin[2L_0(\pi - \theta)]\} \frac{2\pi(\Delta L/2.9)(\pi - \theta)}{\sinh[2\pi(\Delta L/2.9)(\pi - \theta)]} \right] \right\}.$$